Non-equilibrium Kondo e ect in asymmetrically coupled quantum dot

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The quantum dot asym m etrically coupled to the external leads has been analysed theoretically by m eans of the equation of m otion (E O M) technique and the non-crossing approximation (N C A). The system has been described by the single impurity Anderson model. To calculate the conductance across the device the non-equilibrium G reen's function technique has been used. The obtained results show the importance of the asymmetry of the coupling for the appearance of the K ondo peak at nonzero voltages and qualitatively explain recent experiments.

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I. IN TRODUCTION

Recent advances in nanotechnology have allowed the fabrication of structures containing quantum dots coupled to the external environment. The quantum dot consists of nite number of electrons con ned to the small region of space. It behaves like an impurity in a metal [1] and allows the study of the many body correlations between electrons. However, unlike an impurity which parameters are xed, the coupling of the quantum dot to the external leads and its other parameters can be changed in a highly controlled way. Most importantly the non-equilibrium transport [2] can also be studied.

The discovery [3,4] of the K ondo e ect [5] in the quantum dots connected to external leads by tunnel junctions has resulted in an increased experimental [6]-[13] and theoretical [15]-[20] interest in this many body phenomenon. The K ondo e ect in the quantum dot manifests itself at temperatures T lower than the K ondo temperature T_K as an increased conductance G through the system. It is due to the formation of the so called Abrikosov-Suhl or K ondo resonance at the Fermienergy. This is a many body singlet state involving spin on the the quantum dot and the electrons in external leads.

The experiments [3, 4, 6, 8] have con rmed the validity of the theoretical picture. They also discovered phenomena the explanation of which requires new theoretical ideas. In particular they have shown the nonorthodox and unexpected behavior of the system s in the Kondo regime. These are inter alia the observation of the K ondo peak at nonzero source-drain voltage [11, 12], absence of the odd-even parity e ects expected for these system s [13] and observation of the singlet-triplet transition in a magnetic eld. Besides the non-linear currentvoltage characteristics it has been possible to measure charge distribution which led to the conclusion of spincharge separation in a Kondo regime, observe the evolution of the transm ission phase [9] and the detection of two di erent energy scales [10] related to two stages of the spin screening process in systems with spin S with one of the K ondo tem peratures as high as 4K.

The great progress in theoretical understanding of the K ondo physics in real quantum dots has been made dur-

ing last decade. The theory has concentrated on such important aspects as the K ondo-driven transport in multilevel quantum dots [15], the coupled quantum dots [14], double-dot structures in which existence of the K ondo e ect without spin-degree of freedom and new singlet-triplet e ects have been predicted [18], the nature (weak vs strong coupling) of the K ondo e ect at high voltage [19], the spin-charge separation in the strongly correlated quantum dot [17], the systems driven out of equilibrium by di erent means [20] etc..

Here we shall focus our attention on the experim ental observation [11, 12] of the K ondo e ect at nonzero source drain voltages. To state the problem in the right perspective let us rem ind that in systems containing quantum dot, the K ondo e ect manifests itself at low tem peratures as an enhanced conductance observed at zero source-drain voltage, $V_{SD} = 0$ [1, 2, 5]. Occasionally, the Kondo peak in conductance appearing at nonzero voltages V_{SD} θ 0 [11] has been observed and this unusual behavior, called anom alous K ondo e ect rem ains unexplained. Recently this phenomenon has been studied system atically [12]. The authors have fabricated the dot coupled weakly to one and strongly to another lead and observed the evolution of the peak at V_{SD} θ 0. The source-drain voltage V_{SD} , at which the peak appears, scales roughly linearly with a gate voltage, V_q . In the experim ental setup [12] the additional electrode determ ines the asymmetry in the coupling of the dot to left and right leads.

It is the purpose of this paper to study the anom alous K ondo peak observed at non zero voltage. We shall present the results of the model calculations based on the non-equilibrium transport theory [21] applied to the quantum dot described by the Anderson model [22] with asymmetric coupling to the leads. As we shall see the asymmetry in the couplings is the main factor which leads to this anomalous K ondo eect. The experimentally observed shifts of the K ondo peak to higher values of $V_{\rm SD}$ with increasing gate voltage can be satisfactorily explained by assuming that the values of the left and right barriers change together with the gate voltage, while the asymmetry in the couplings remains constant. This scenario is realized in experiment [12].

The organization of the rest of the paper is as follows. In section II we introduce the model, give the formula for the current through the quantum dot and discuss brie y the methods (equation of motion (EOM) with slave boson representation of electron operators and noncrossing approximation (NCA)) used to calculate on-dot G reen's function relegating some technical details to the appendix. In section III we present the results of our numerical calculations of the tunneling conductance across the asymmetrically coupled single level quantum dot in U = 1 limit. Conclusions are given in section IV.

II. THE THEORY

For the sake of sim plicity we discuss here the dot with single energy level. The theoretical analysis of the transport through quantum dot usually starts with the following, Landauer type, formula [2] for the current

$$J = \frac{e^{X}}{c} \quad \text{d!} [f_{L}(!) \quad f_{R}(!)]$$

$$\frac{L(!)^{R}(!)}{L(!) + R(!)} \quad \frac{1}{c} \text{Im } G^{r}(! + i0^{+}) \quad (1)$$

Here f (!) denotes the Fermi distribution function for lead with chemical potential , $G^{\rm r}$ (!) is the (reparded) impurity Green's function and (!) = $2 \, {}_{\rm k} \, {}^{\rm f} \! {}_{\rm k} \, {}^{\rm f}$ (! " $_{\rm k}$) is the elective coupling of localized electron to conduction band.

The current J owing across the system depends on the source-drain voltage $V_{\text{SD}} = (L_{\text{R}}) = e$, where e is the electron charge. The di erential conductance of the system dened as $G(V_{\text{SD}}) = \frac{dJ(V_{\text{SD}})}{dV_{\text{SD}}}$ is directly measured experimentally [3].

To calculate the on-dot G reen's function G $(!+i0^+)$ we shall describe the dot coupled to the external leads by the single in purity Anderson H am iltonian [22]

$$H = \begin{bmatrix} X & & X \\ & & & \\ & &$$

Here = R;L denote the right (R) or the left (L) lead in the system. O ther symbols have the following meaning: $c^{\dagger}_{\ k}$ ($c_{\ k}$) denotes creation (annihilation) operator for a conduction electron with wave vector \tilde{k} , spin in the lead , V $_{k}$ is the hybridization matrix element between conduction electron of energy " $_{k}$ in the lead and localized electron on the dot. E $_{d}$ is the single particle energy at the dot. $n_{"}=d_{"}^{\dagger}d_{"}$ is the number operator for electrons with spin up localized on the dot and U is the (repulsive) interaction energy between two electrons. Our calculations are restricted to very low temperatures, much smaller than the orbital level spacing in quantum dot so it is legitim ate to consider single energy level E $_{d}$.

There are various methods [2] of calculating the on-dot G reen's function entering the current (1). Here we shall apply two of them: equation of motion method (EOM) and non-crossing approximation (NCA). In both cases we assume that the Coulomb repulsion U between electrons on the dot is the largest energy scale. Therefore we take the \lim it U=1. The original correlated electron operators are expressed as products of auxiliary ferm ion and boson ones [2].

When using equation of motion method (EOM) we apply a mean eld like approximation for the slave bosons and calculate all matrix elements of the Keldysh Green's functions, including the distribution one [23]. In the process we consistently decouple all elements of the higher order Keldysh Green functions [24]. The relevant formulae and som e technical details can be found in the appendix. As we shall see the method gives correct position of the K ondo peak. However, like the standard EOM it leads to incorrect width of the peak and the occupations. Therefore we have used the non-crossing approximation (N C A), which is generally accepted technique of solving the problem at hand [5]. In the NCA one maps the innite U Anderson model onto the slave boson one and calculates both boson and ferm ion propagators. They are expressed by the coupled integral equations [2].

W here appropriate we shall present the results obtained by both techniques.

III. NUMERICAL RESULTS

Let us $\,$ rst discuss the relation between the experim ental param eters and those entering the m odel and the theory. The e ective coupling $_L$ and $_R$ have been estimated in ref.[12] to be 170 $\,$ eV and 80 $\,$ eV respectively. Their values and the ratio $_L$ = $_R$ $\,$ 2 have been argued to remain constant during the measurements. The source-drain voltage V_{SD} is the dierence of the chemical potentials of the external leads. The (back) gate voltage V_g controls the position of the on-dot energy level E $_d$. As already mentioned we stick here to the U = 1 $\,$ limit. In this limit there can be at most a single electron with energy E $_d$ on the dot at a time.

We start the presentation of the results with the comparison of the (equilibrium) density of states of a quantum dot coupled to two leads obtained by means of NCA and EOM approaches. It is shown in the Fig. (1). The main features of the DOS remain the same in both approaches. However the height and the width of the Kondo peak is much larger in the NCA. Moreover the spectral weight is shifted towards higher energies. In turn this leads to dierent occupations shown in the inset of the Fig.(1).

Now let's turn to the nonequilibrium ($_{\rm L}$ $_{\rm R}$) density of states. In this case the high energy features to large extend remain the same as in equilibrium (see Fig.(1)), so the only low energy DOS is shown in the Fig.(2). The upper panel presents results obtained

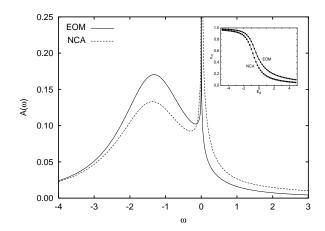


FIG.1: The equilibrium density of states on the quantum dot obtained within EOM (solid line) and NCA (dashed line). Note the relative shift of the spectral weight with respect to the chemical potential = 0 which results in dierent occupations shown in the inset. The parameters are: Ed= 2, L= R=1 and T=10 3 .

via equation of motion technique for Keldysh (matrix) G reen's function. In the lower panel the results obtained with the non-crossing approximation are shown. The coupling is asymmetric with $_{L}$ = $_{R}$ = 2 (dashed lines) and $\frac{1}{2}$ (dotted lines). The case of the sym m etric coupling $_{\rm L}$ = $_{\rm R}$ is also shown (solid lines) for comparison. Few features have to be noted. First we see that the K ondo peak is always located at energies coinciding with those of the Ferm i levels of the leads. Thus in non-equilibrium we get (in the density of states) two Kondo resonances pinned to Ferm i energies of the left and right electrodes. Note also that the heights of the respective K ondo resonances strongly depend on the value of the hybridization. The overall shape of the density of states is sim ilar. The positions of the K ondo peaks are roughly the same but they dier in width and heigths. The peaks obtained in ${\tt EOM}$, are much narrower and sm aller. As a result the curves in gure (2a) dier from that in gure (2b).

These details in the energy dependence of the density of states may shortly be a matter of direct measurements. In fact it has been recently predicted theoretically [25] that the on-dot density of states can be measured in a device containing quantum dot coupled to three leads. The very weakly coupled third lead will act as a tunneling tip in conventional tunneling microscope and will probe the non-equilibrium density of states. The conductance spectrum measured by this additional electrode has been shown [25] to follow the non equilibrium density of states, like one shown in Fig.(2).

Returning to our main subject we show in Fig.(3) the dierential conductance spectrum corresponding to the same 'experim ental setup' as discussed previously in connection with gure (2). For comparison we have also plotted in this gure the conductance through the symmetrically coupled quantum dot. In the symmetric situation

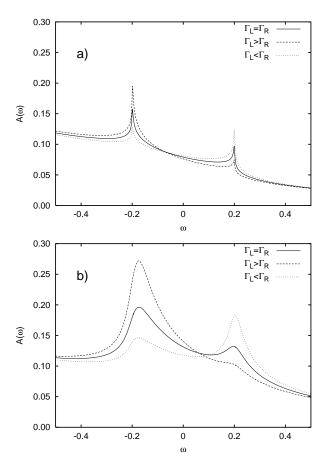


FIG. 2: The nonequilibrium density of states obtained within a) – EOM and b) – NCA for the symmetric $_{\rm L}$ = $_{\rm R}$ (solid lines) and asymmetrically coupled quantum dot with $_{\rm L}$ = $_{\rm R}$ (dashed) and $_{\rm L}$ = $_{\rm L}$ (dotted lines). $_{\rm R}$ = $_{\rm L}$ = 0.2 and the other parameters are the same as in Fig. (1).

($_{\rm L}$ = $_{\rm R}$) the K ondo resonance is located exactly at zero bias (VD $_{\rm S}$ = 0), but for $_{\rm L}$ > $_{\rm R}$ ($_{\rm L}$ < $_{\rm R}$) it is shifted to the negative (positive) voltages VD $_{\rm S}$. This inding is in nice qualitative agreem ent with the experimental studies on the transport through the quantum dot in the presence of the asym metric barriers [12]. While the observed shifts calculated within EOM and NCA are of comparable magnitude the clear dierences in their shape are visible. The NCA peaks are much higher and more symmetric in vicinity of their maxima. For asymmetric coupling the K ondo resonance in the conductance is pinned to the position of the Fermi level of that lead which is more strongly coupled (larger) to the dot. It is thus mainly the relative coupling which rules the value of the shift.

In Fig.(4) we show the systematic change of the G ($V_{\rm D~S}$) with increasing asymmetry $_{\rm L}$ = $_{\rm R}$ of the coupling. The upper curves in both panels corresponds to $_{\rm L}$ = $_{\rm R}$ = 5.5 while lower one is for symmetric coupling $_{\rm L}$ = $_{\rm R}$ = 1 in steps of 0.5. The increase of the asymmetry $_{\rm L}$ = $_{\rm R}$ from 1 to 5.5 continuously moves the K ondo peak away from $V_{\rm SD}$ = 0 position. We have checked

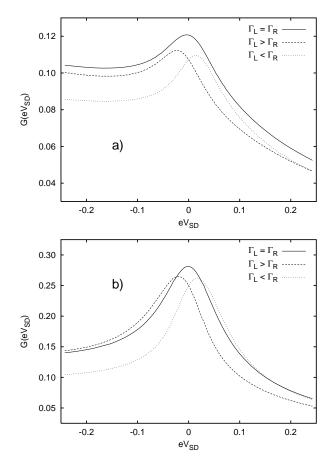


FIG. 3: The dierential conductance (G (eV $_{\rm S\,D}$) = dJ=d(eV $_{\rm S\,D}$)) obtained within a) – E O M and b) – N C A for the sym metric $_{\rm L}$ = $_{\rm R}$ (solid lines) and asym metrically coupled quantum dot with $_{\rm L}$ = 2 $_{\rm R}$ (dashed) and $_{\rm L}$ = $\frac{1}{2}$ $_{\rm R}$ (dotted lines).

that increasing asymmetry to still higher values does not lead to bigger shifts. This is easy to understand as for large asymmetry one of barriers is not transparent enough to produce the clear K ondo resonance in the density of states.

The position of the on-dot electron energy level E $_{\rm d}$ inuences anom alous K ondo peak for the asymmetric dot with $_{\rm L}$ = $_{\rm R}$ = 2 to lesser extend. It is only important that it takes a value appropriate for observing a K ondo resonance. For all appropriate E $_{\rm d}$ the shifts are of comparable magnitudes.

The data displayed in the gure (4) qualitatively agree with those plotted in gure (5) of [11] and gure (3) of [12]. However, theoretical shifts of the Kondo peak position are smaller than the experimental.

There may be additional factors which a ect the position of the peaks. We have checked that the energy dependence of $_{\rm L,R}$ introduces only small quantitative di erences in the density of states and di erential conductance, and does not lead to better agreem ent between theory and experiment. Similarly the calculations within EOM approach for nite values of U show that nite

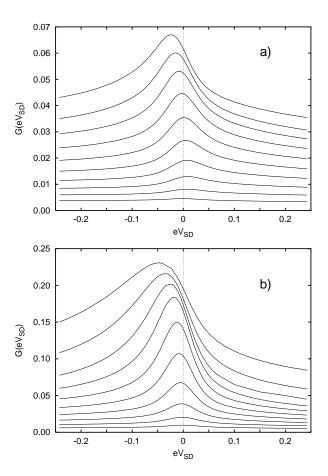


FIG. 4: The di erential conductance obtained within a) – EOM and b) – NCA for the di erent asymmetric couplings. The lower curve is for $_{\rm L}$ = $_{\rm R}$ while the upper one – $_{\rm L}$ = 55 $_{\rm R}$. Other parameters are E $_{\rm d}$ = 10 and T = 10 2 in units of $_{\rm R}$.

U leads to m inor corrections as also does the presence of the additional energy levels in the vicinity of Ferm i energy. In all the cases studied one gets usual behavior with K ondo peak located at $V_{\rm SD}=0$ for sym metric coupling to both leads and the anom alous K ondo e ect for asym metric coupling. This proves the importance of the asym metry in the observattion of it.

In experimental setup [12] the changes of the gate voltage V_g , which in $\,$ rst place a ect the position of the electron energy level also modify the height of the barriers and their transparency V_k . This e ect is of special importance in the quantum dots de ned in the two dimensional electron gas where the voltage at a single electrode couples capacitively to other electrodes [26]. If we assume that (as in experiments) $_L = _R$ remains constant (= 2) and that the decrease of the energy E $_d$ is accompanied by the simultaneous increase of the couplings $_R$ and $_L$ then the calculated shifts get larger.

The occurence of the K ondo resonace is possible at low enough temperature. It is also well known [2] that changes of temperature move slightly the K ondo peak. We have checked this and found that if temperature is

raised the position of the peak m oves slightly away from the $V_{\text{SD}} = 0\,.\,\text{At}\,$ nite tem perature the occupation of the dot changes and the Abrikosov-Suhl resonances smear out and this leads to small changes in the position of the K ondo peak.

We thus have combined all above contributions, i.e. assym etry in the couplings $_L$ \in $_R$, their E_d -dependence, and assumed high enough, but still below T_K , temperature to get larger shifts of the K ondo peak. We have

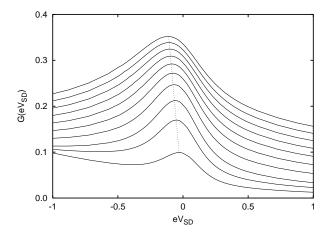


FIG. 5: The N C A calculated di emential conductance as a function of source-drain voltage $V_{\rm S\,D}\,$ for various values of the E $_{\rm d}$ and $_{\rm L}$, $_{\rm R}$ at xed $_{\rm L}$ = $_{\rm R}$ =2. The lowest curve correspond to E $_{\rm d}$ =3, $_{\rm L}$ =1, while upper one is for E $_{\rm d}$ =12, $_{\rm L}$ =6.4 in units of $_{\rm 0}$ equal to initial coupling of the left lead. The temperature T = 5 10 $^{\rm 2}$ is below estimated K ondo temperatures.

shown the results in Fig.(5). The various curves have been calculated for T = 510^3 which is below K ondo temperature. In the gure the change of the position of the on dot energy level is accompanied by the simultaneous change of the barrier transparency. The bottom curve in gure (5) corresponds to E $_{\rm d}$ = $3_{\rm 0}$, $_{\rm 0}$ = $_{\rm L}$, while the upper one corresponds to E $_{\rm d}$ = $12_{\rm 0}$, $_{\rm L}$ = 6.4 $_{\rm 0}$. Here $_{\rm 0}$ is equal to experimentally estimated value of of the smaller of couplings [12]. The ratio $_{\rm R}$ = $_{\rm L}$ is kept constant and equal 2 as estimated in [12]. The data are in nice qualitative agreement with experiments. The theoretical shifts, however, are smaller than experimentally a factor of 5–10. To check whether this is due to dierent asymmetry ratio we plot in gure (6) the results obtained for $_{\rm R}$ = $_{\rm L}$ = 4. The shifts have increased.

IV. CONCLUSIONS

W e have found that the em ergence of the K ondo peak at non zero voltages $V_{D\ S}\ \in\ 0$ is caused by asym m etric coupling of the dot to the external electrodes. These results are in qualitative agreem entwith experimental data on the transport through the quantum dot asym metrically coupled to the leads [11, 12]. The theoretical K ondo

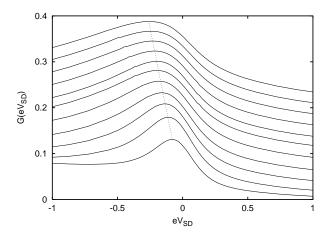


FIG. 6: The same as in Fig. (5) but for asymmetry $_{\rm L}$ = $_{\rm R}$ = 4. The lowest curve correspond to E $_{\rm d}$ = 4, $_{\rm L}$ = 1, while upper one is for E $_{\rm d}$ = 17.5, $_{\rm L}$ = 12.8 in units of $_{\rm 0}$ equal to initial coupling of the left lead.

peaks in di erential conductance, however, are narrower than experim entalones. Their maxim a move to nonzero V_{SD} with increasing the asymmetry or the position of the on-dot energy level. The simultaneous change of Ed and $_{\rm L}$, $_{\rm R}$ can sem i-quantitatively explain experim ental data. M ore experim ental results are needed to draw m conclusions such as the applicability of simple Anderson m odel to asymmetrically coupled quantum dots. It follows from the presented studies that the asymmetry of the couplings is a necessary ingredient for the explanation of the anomalous Kondoe ect. Within the Anderson m odelone always gets normalK ondo e ect for sym metric couplings and small shifts of the K ondo peak to non-zero voltages for asym m etric couplings. Our inability to explain quantitatively the experim ental data may indicate the necessity of much better theoretical treatment of the m odel or even better m odel for the description of these complicated systems. There is a possibility that the experim entally observed features, even though similar to, do not represent genuine K ondo e ect. In fact som e researches [27] have seen very small shifts, consistent with present calculations, even for quite asymmetrically coupled quantum dots.

A cknow ledgm ents

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APPENDIX A

To nd the current accross the system , Eq.(1), it is enough to calculate the on-dot retarded G reen's function .

The N C A m ethod to get G^r (!) has been extensively discussed previously [2] and there is no need to repeat its derivation again. For the sake of completeness let us only note that we have adapted the formulae derived in the second paper of the reference [2].

The EOM method to calculate the GF is straightforward and in U ! 1 \lim it leads to

$$G^{r}(!) = \frac{1 \quad \text{ln} \quad i}{! \quad E_{d} \quad r \quad (!)}$$
 (A1)

with the self-energy

$$f(!) = \sum_{k}^{X} y_{k} j^{2} \frac{1 + f(!)}{!}$$
 (A2)

In the equation (A1), hn i denotes the average ondot occupation number of the spin electrons. In the equilibrium one calculates hn i self-consistently from

the retarded G reen's function G^r (!). Here we are dealing with nonequilibrium situation and hn i cannot be calculated directly from G^r (!). Instead the nonequilibrium [21] G reen's function technique has to be used. The occupation of the dot at time t is expressed via K eldysh "lesser" G reen's function hn (t) i = hc^+ (t) c (t) i = $iG^<$ (t;t). In the steady state one gets

$$m = i \frac{Z_1}{2} G^{<}(!);$$
 (A3)

This shows that the consistent calculations of the retarded GF requires the know ledge of "lesser" one. The equation of motion for the "lesser" GF has been form ulated by N iu et al [23]. For the H am iltonian of the form H = H $_0$ + H $_{\rm I}$ they derived the following general equation for the "lesser" GF

$$hA \not \exists ii_{!}^{<} = g^{<}(!)hA;B \mid i+g^{r}(!)hA;H_{I} \mid \exists ii_{!}^{<} + g^{<}(!)hA;H_{I} \mid \exists ii_{!}^{a};$$
(A 4)

here g $^{<\,(r)}$ (!) is the "lesser" (retarded) GF of the noninteracting part H $_0$ of H am iltonian.

To treat strong correlations we use the version [24] of

the slave boson technique and rewrite the Hamiltonian in the form

$$H^{SB} = X \\ (" _k) c_k^+ c_k + "_d f^+ f + X \\ V_k (c_k^+ b^+ f + f^+ bc_k);$$
 (A5)

where new ferm ionic (f⁺;f) and bosonic (b⁺;b) operators have been introduced. Calculating the on-dot G reen's function G $^<$ (!) = hhb+f f jf+bii_! we have taken the third term of H $^{\rm SB}$ as an interaction part H $_{\rm I}$ and the rst two terms of it as H $_{\rm O}$.

The average occupation number is found to be

$$hni = \frac{1}{2} X^{\frac{Z_1}{2}} d! X Im^{r} (!)f (!)f^{r} (!)f^{2}(A 6)$$

Note that in turn it depends on the retarded Green's function. This closes the system of equations.

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